

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1520

DESCRIPTION

- With TO-202 package
- High voltage
- High transition frequency

APPLICATIONS

- For color TV chroma output and video output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

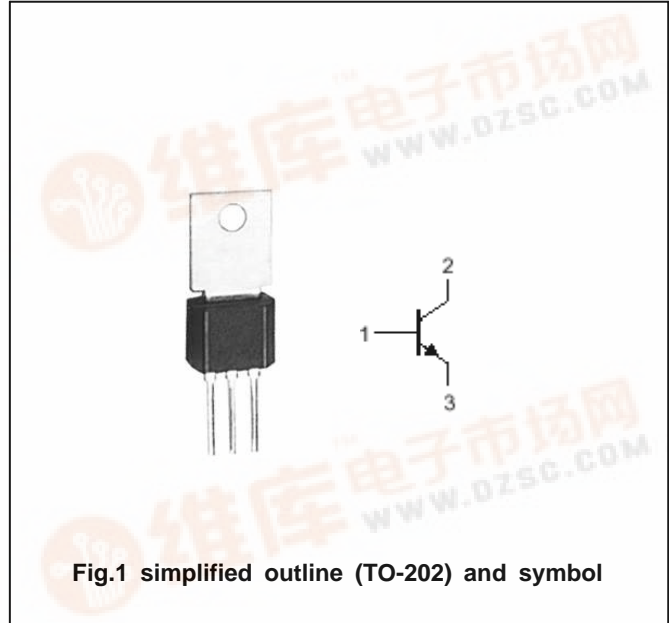


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	250	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _c	Collector current		0.2	A
P _c	Collector power dissipation	T _a =25°C	1.0	W
		T _c =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA ; I _B =5mA			2.0	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; I _B =0	250			V
I _{CBO}	Collector cut-off current	V _{CB} =150V ; I _E =0			0.1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	μ A
h _{FE}	DC current gain	I _C =10mA ; V _{CE} =10V	40		200	
C _{OB}	Output capacitance	I _E =0; V _{CB} =50V; f=1MHz			4.5	pF
f _T	Transition frequency	I _C =10mA ; V _{CB} =30V		80		MHz

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PACKAGE OUTLINE

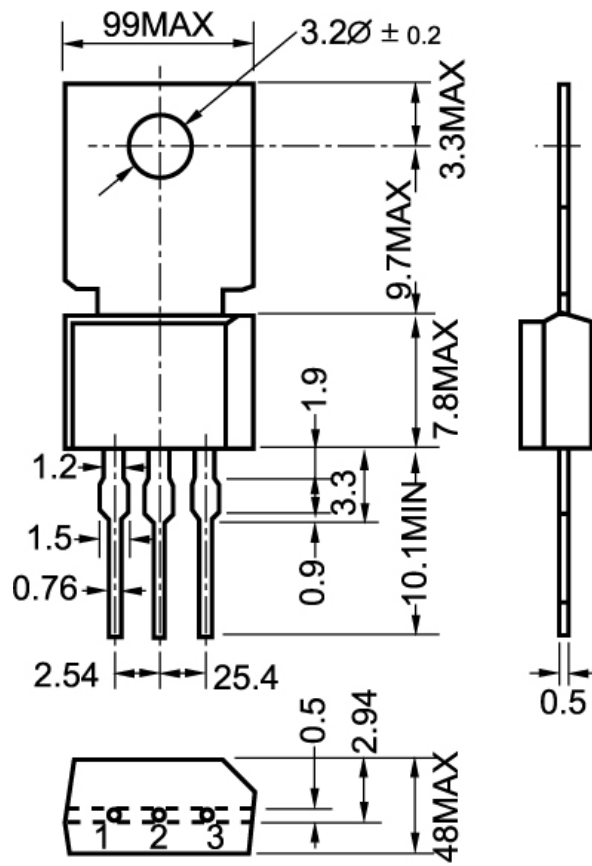


Fig.2 outline dimensions